BLF7G22L-160; BLF7G22LS-160 Power LDMOS transistor Rev. 3 — 1 September 2015

AMPLEON

Product data sheet

Product profile

1.1 General description

160 W LDMOS power transistor for base station applications at frequencies from 2000 MHz to 2200 MHz.

Typical performance Table 1.

Typical RF performance at $T_{case} = 25$ °C in a common source class-AB production test circuit.

Mode of operation	f	I _{Dq}	V _{DS}	P _{L(AV)}	Gp	η_{D}	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2110 to 2170	1300	28	43	18.0	30	-32 <mark>[1]</mark>

^[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2000 MHz to 2200 MHz frequency range

2. Pinning information

Table 2. Pinning

Description		Simplified outline	Graphic symbol
L-160 (SOT502A)			
drain			_
gate			, L
source	<u>[1]</u>		2
			3 sym112
LS-160 (SOT502B)			·
drain			
gate		1 1	1 <u> </u>
source	<u>[1]</u>	2	2
			sym112
	drain gate source LS-160 (SOT502B) drain gate	drain gate source [1] LS-160 (SOT502B) drain gate	drain gate source LS-160 (SOT502B) drain gate source [1] 1 3

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packa	ge	
	Name	Description	Version
BLF7G22L-160	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLF7G22LS-160	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mi	n Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0	.5 +13	V
I _D	drain current		-	36	Α
T _{stg}	storage temperature		-6	5 +150	°C
Tj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 80 °C; P_L = 55 W	0.29	K/W

BLF7G22L-160_7G22LS-160#3

6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_{D} = 216 mA	1.5	1.9	2.3	V
I_{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	4.5	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	34	-	-	Α
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	450	nA
g _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 10.8 A	-	20	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 7.56 \text{ A}$	-	0.06	-	Ω

7. Test information

Table 7. Application information

Mode of operation: 2-carrier W-CDMA; PAR 8.4 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 PDPCH; f_1 = 2112.5 MHz; f_2 = 2117.5 MHz; f_3 = 2162.5 MHz; f_4 = 2167.5 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 1300 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 43 W$	16.5	18.0	-	dB
RLin	input return loss	$P_{L(AV)} = 43 W$	-	-15	-6.5	dB
η_{D}	drain efficiency	$P_{L(AV)} = 43 W$	27	30	-	%
ACPR _{5M}	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 43 W$	-	-32	-28	dBc

Table 8. Application information

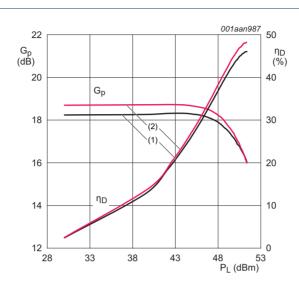
Mode of operation: 1-carrier W-CDMA; PAR 7.2 dB at 0.01 % probability on CCDF; 3GPP test model 1; 64 PDPCH; f=2167.5 MHz; RF performance at $V_{DS}=28$ V; $I_{Dq}=1300$ mA; $T_{case}=25$ °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PAR _O	output peak-to-average ratio	P _{L(AV)} = 100 W; at 0.01 % probability on CCDF	3.9	4.15	-	dB

7.1 Ruggedness in class-AB operation

The BLF7G22L-160 and BLF7G22LS-160 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 1300 \text{ mA}$; $P_L = 160 \text{ W}$; f = 2110 MHz.

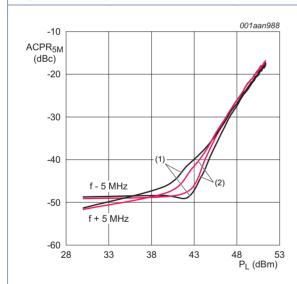
7.2 2-Carrier W-CDMA 5 MHz



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2110 MHz
- (2) f = 2170 MHz

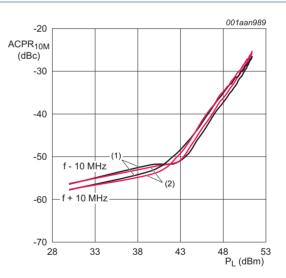
Fig 1. Power gain and drain efficiency as function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

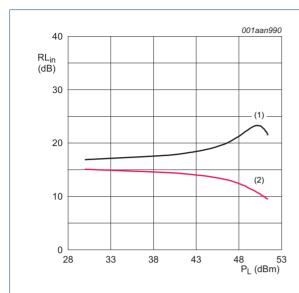
Fig 2. Adjacent channel power ratio (±5 MHz) as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

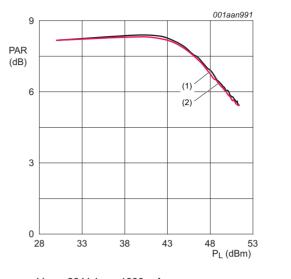
Fig 3. Adjacent channel power ratio (±10 MHz) as a function of load power; typical values



 V_{DS} = 28 V; I_{Dq} = 1300 mA.

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 4. Input return loss as function of load power; typical values

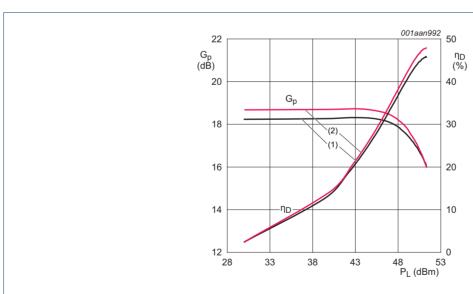


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 5. Peak-to-average power ration as function of load power; typical values

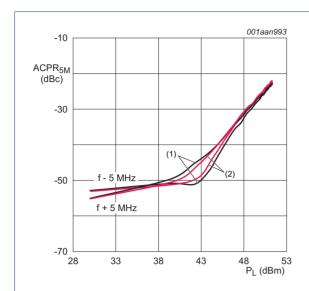
7.3 2-Carrier W-CDMA 10 MHz



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

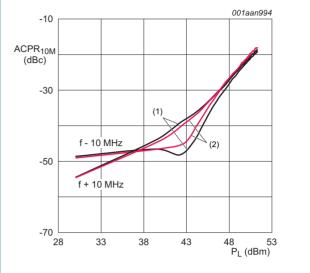
Fig 6. Power gain and drain efficiency as function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 7. Adjacent channel power ratio (±5 MHz) as a function of load power; typical values

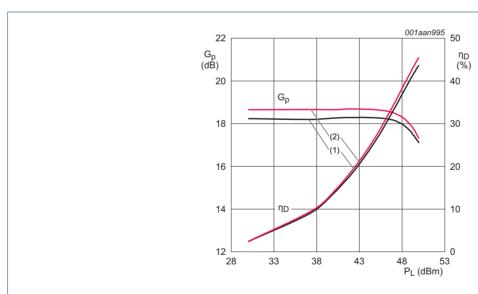


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 8. Adjacent channel power ratio (±10 MHz) as a function of load power; typical values

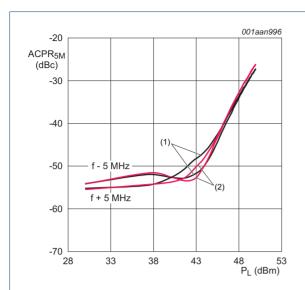
7.4 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

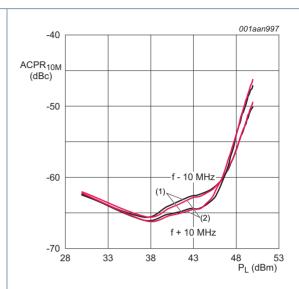
Fig 9. Power gain and drain efficiency as function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

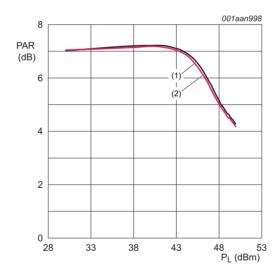
Fig 10. Adjacent channel power ratio (±5 MHz) as a function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 11. Adjacent channel power ratio (±10 MHz) as a function of load power; typical values

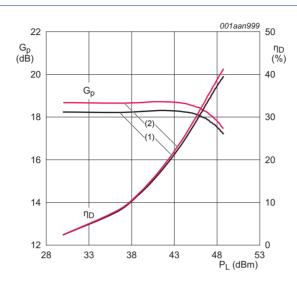


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 12. Peak-to-average power ration as function of load power; typical values

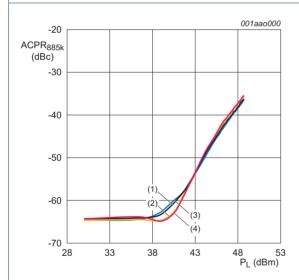
7.5 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

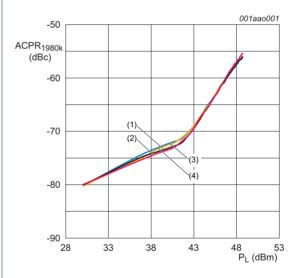
Fig 13. Power gain and drain efficiency as function of load power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$

- (1) f = 2110 MHz; f + 885 kHz
- (2) f = 2170 MHz; f + 885 kHz
- (3) f = 2110 MHz; f 885 kHz
- (4) f = 2170 MHz; f 885 kHz

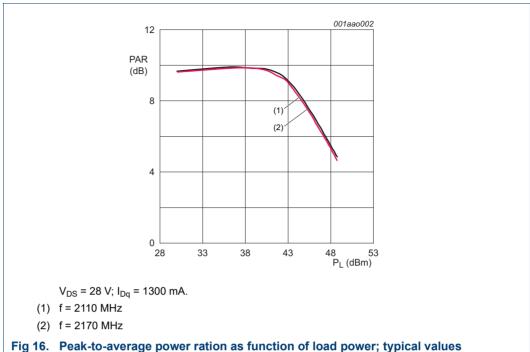
Fig 14. Adjacent channel power ratio (±5 MHz) as a function of load power; typical values



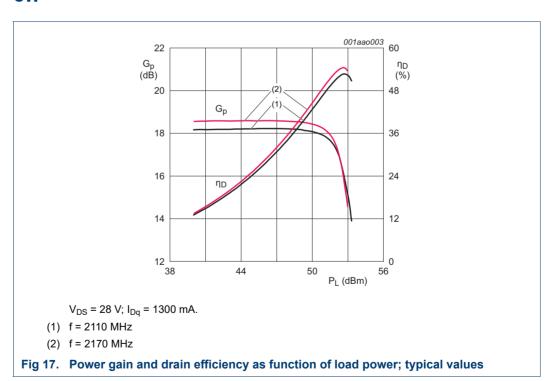
 $V_{DS} = 28 \text{ V}; I_{Da} = 1300 \text{ mA}.$

- (1) f = 2110 MHz; f + 1980 kHz
- (2) f = 2170 MHz; f + 1980 kHz
- (3) f = 2110 MHz; f 1980 kHz
- (4) f = 2170 MHz; f 1980 kHz

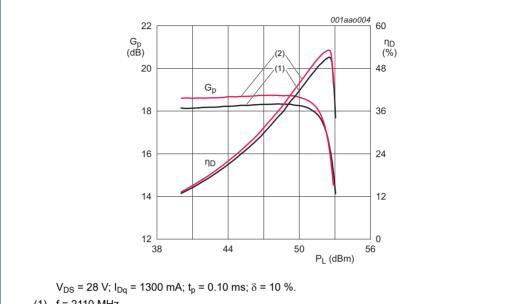
Fig 15. Adjacent channel power ratio (±10 MHz) as a function of load power; typical values



7.6 CW



7.7 CW-pulsed



- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 18. Power gain and drain efficiency as function of load power; typical values

7.8 Test circuit

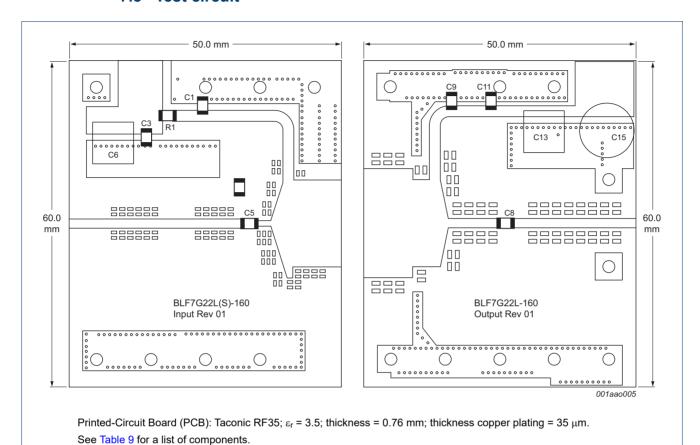


Table 9. List of components

Fig 19. Component layout for class-AB production test circuit

For test circuit see Figure 19. **Description** Component Value Remarks [1] C1, C5, C8, C9 multilayer ceramic chip capacitor 68 pF [2] C3, C11 multilayer ceramic chip capacitor 820 pF [3] C6, C13 multilayer ceramic chip capacitor $10 \mu F$ C15 electrolytic capacitor 470 μF; 63 V R1 SMD resistor 12Ω Philips 1206

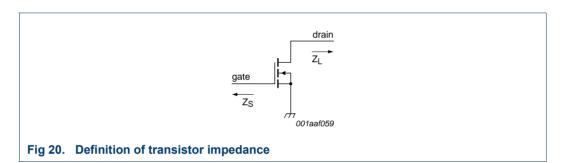
- [1] American Technical Ceramics type 800B or capacitor of same quality.
- [2] American Technical Ceramics type 100A or capacitor of same quality.
- [3] TDK or capacitor of same quality.

7.9 Impedance information

Table 10. Typical impedance

Typical values unless otherwise specified.

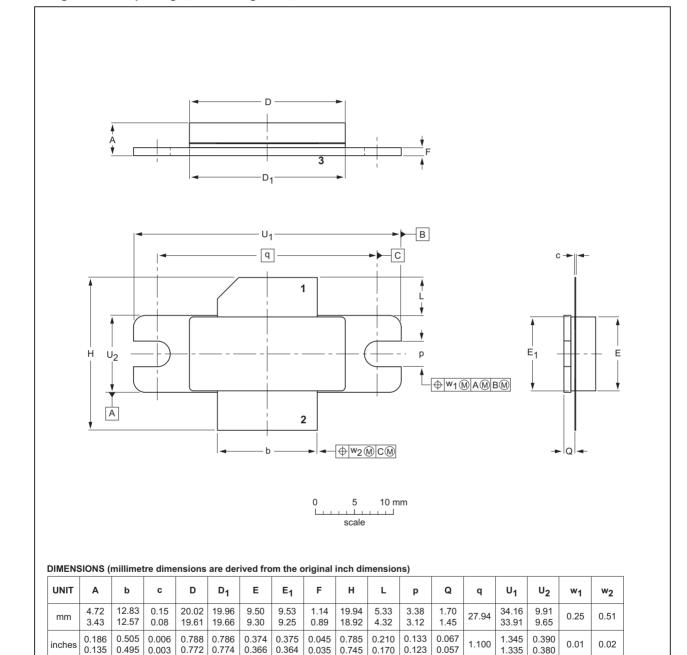
f	Z _S	Z _L
MHz	Ω	Ω
2050	1.39 – j4.13	1.41 – j3.80
2080	1.67 – j3.93	1.38 – j3.63
2110	2.01 – j3.89	1.35 – j3.45
2140	2.28 – j4.09	1.33 – j3.28
2170	2.27 – j4.47	1.31 – j3.12
2200	1.92 – j4.76	1.28 – j2.95
2230	1.42 – j4.75	1.26 – j2.79



Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT502A



OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT502A					-03-01-10- 12-05-02	

0.745

0.170

0.123

0.057

1.335

0.380

Fig 21. Package outline SOT502A

0.495

0.003

0.772

0.366

0.364

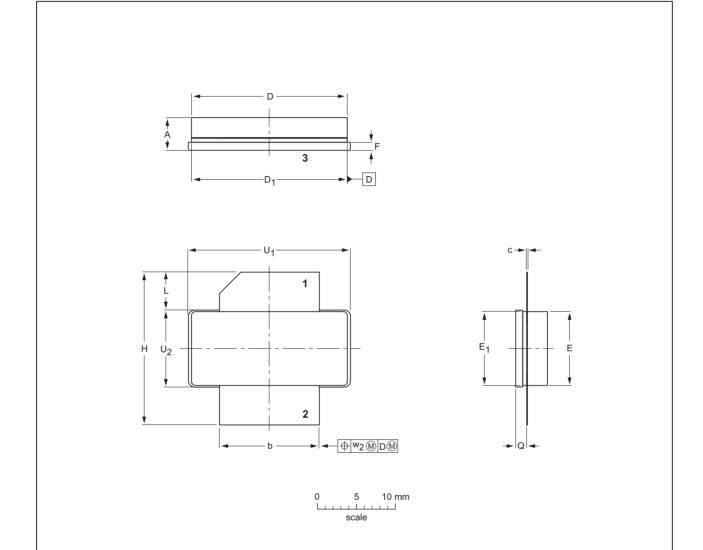
0.035

13 of 18

0.02

Earless flanged ceramic package; 2 leads

SOT502B



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	Α	b	С	D	D ₁	E	E ₁	F	Н	L	Q	U ₁	U ₂	w ₂
mm	4.72 3.43	12.83 12.57	0.15 0.08	20.02 19.61	19.66	9.30	9.53 9.25	0.89	19.94 18.92	4.32	1.70 1.45	20.70 20.45	9.65	0.25
inches	0.186 0.135	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.067 0.057	0.815 0.805	0.390 0.380	0.010

OUTLINE		REFER	RENCES		ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT502B						07-05-09 12-05-02	

Fig 22. Package outline SOT502B

9. Abbreviations

Table 11. Abbreviations

Tuble 11. Abbreviations				
Acronym	Description			
3GPP	Third Generation Partnership Project			
CCDF	Complementary Cumulative Distribution Function			
CW	Continuous Wave			
DPCH	Dedicated Physical CHannel			
ESD	ElectroStatic Discharge			
LDMOS	Laterally Diffused Metal Oxide Semiconductor			
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor			
PAR	Peak-to-Average power Ratio			
PDPCH	transmission Power of the Dedicated Physical CHannel			
RF	Radio Frequency			
SMD	Surface Mounted Device			
VSWR	Voltage Standing Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			
-				

10. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF7G22L-160_7G22LS-160#3	20150901	Product data sheet	-	BLF7G22L-160_7G22LS-160 v.2.1	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLF7G22L-160_7G22LS-160 v.2.1	20111102	Product data sheet	-	BLF7G22L-160_7G22LS-160 v.2	
BLF7G22L-160_7G22LS-160 v.2	20111020	Product data sheet	-	BLF7G22L-160_7G22LS-160 v.1	
BLF7G22L-160_7G22LS-160 v.1	20110427	Preliminary data sheet	-	-	

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BLF7G22L-160 7G22LS-160#3

BLF7G22L-160; BLF7G22LS-160

Power LDMOS transistor

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For sales office addresses, please visit: http://www.ampleon.com/sales

BLF7G22L-160; BLF7G22LS-160

AMPLEON

Power LDMOS transistor

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.